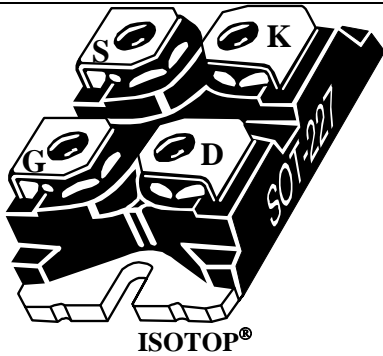
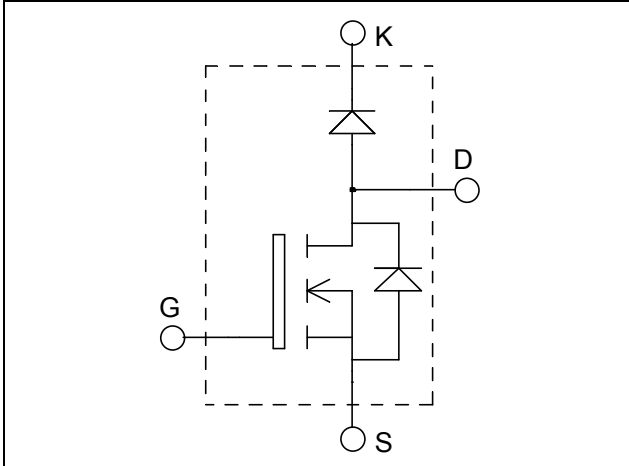


## ISOTOP<sup>®</sup> Boost chopper Super Junction MOSFET Power Module

$V_{DSS} = 900V$   
 $R_{DSon} = 120m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 33A \text{ @ } T_c = 25^\circ C$



### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

### Features

- **COOLMOS** Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_c$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	900	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	33
		$T_c = 80^\circ C$	25
$I_{DM}$	Pulsed Drain current	75	A
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	120	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	290
$I_{AR}$	Avalanche current (repetitive and non repetitive)	8.8	A
$E_{AR}$	Repetitive Avalanche Energy	2.9	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1940	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 900V$			100	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$		500		
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 26A$		100	120	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 3\text{mA}$	2.5	3	3.5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 100V$ $f = 1\text{MHz}$		6.8		nF
$C_{oss}$	Output Capacitance			0.33		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 26A$		270		nC
$Q_{gs}$	Gate – Source Charge			32		
$Q_{gd}$	Gate – Drain Charge			115		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (<math>125^\circ\text{C}</math>)</b> $V_{GS} = 10V$ $V_{Bus} = 600V$ $I_D = 26A$ $R_G = 7.5\Omega$		70		ns
$T_r$	Rise Time			20		
$T_{d(off)}$	Turn-off Delay Time			400		
$T_f$	Fall Time			25		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 600V$ $I_D = 26A ; R_G = 7.5\Omega$		1.5		mJ
$E_{off}$	Turn-off Switching Energy			0.75		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 600V$ $I_D = 26A ; R_G = 7.5\Omega$		2.1		mJ
$E_{off}$	Turn-off Switching Energy			0.85		

**Chopper diode ratings and characteristics**

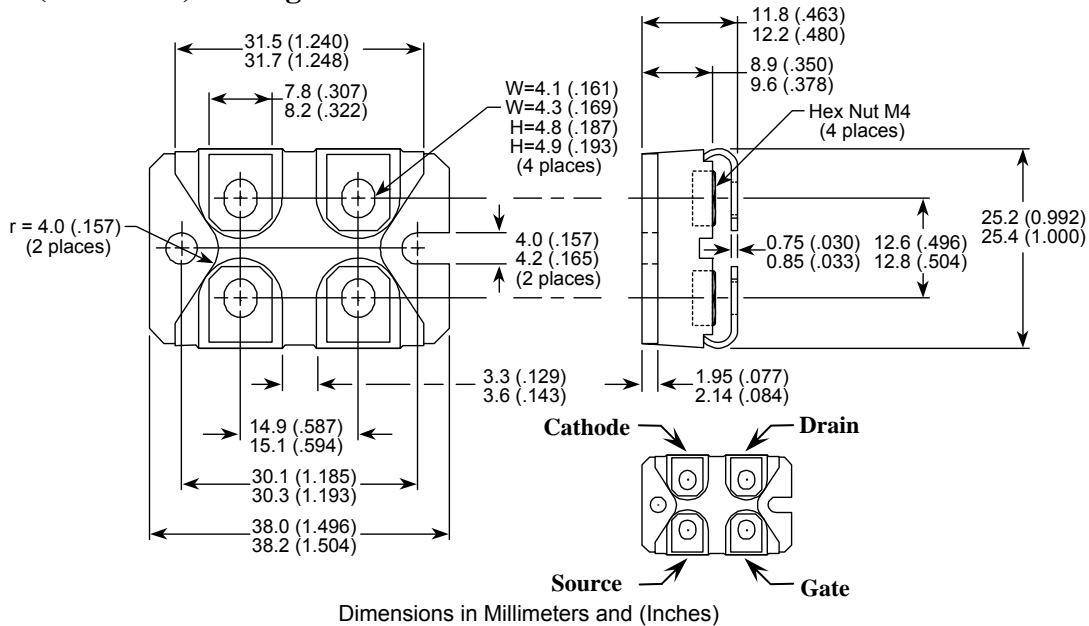
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		30		A
$V_F$	Diode Forward Voltage	$I_F = 30A$		2.6	3.1	V
		$I_F = 60A$		3.2		
		$I_F = 30A$	$T_j = 125^\circ\text{C}$	1.8		
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	300		ns
			$T_j = 125^\circ\text{C}$	380		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	360		nC
			$T_j = 125^\circ\text{C}$	1700		

## Thermal and package characteristics

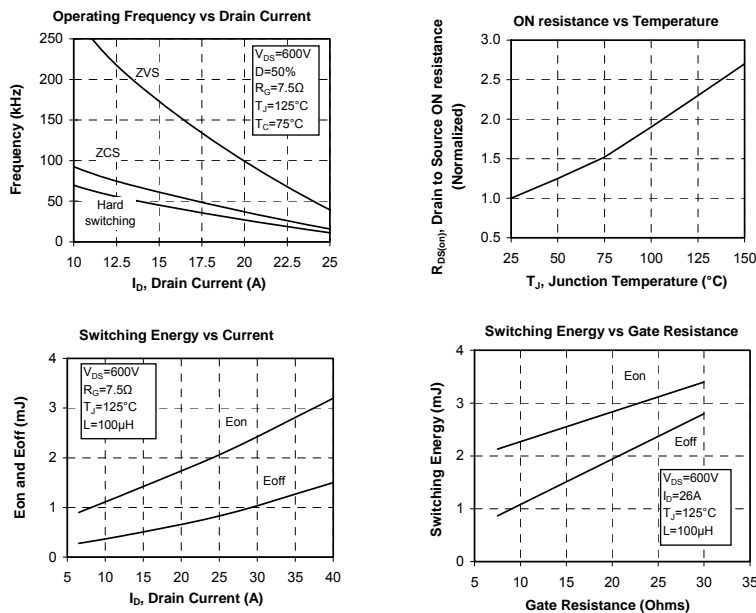
Symbol Characteristic

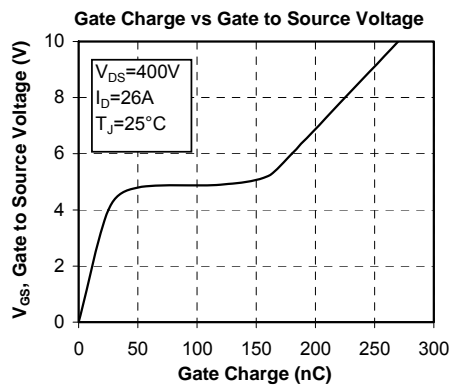
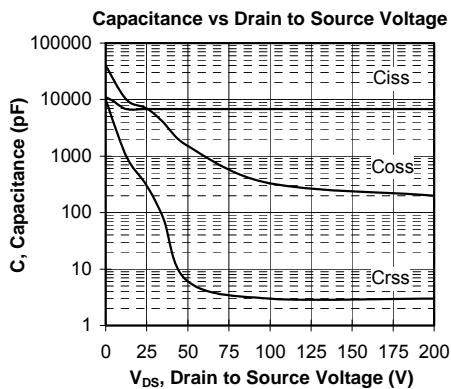
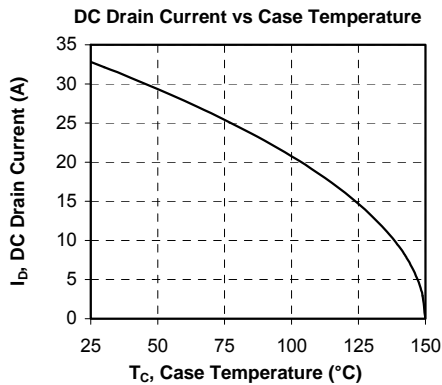
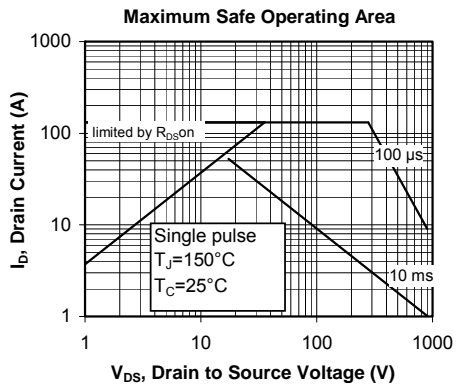
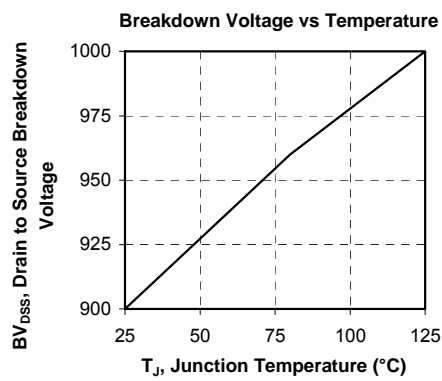
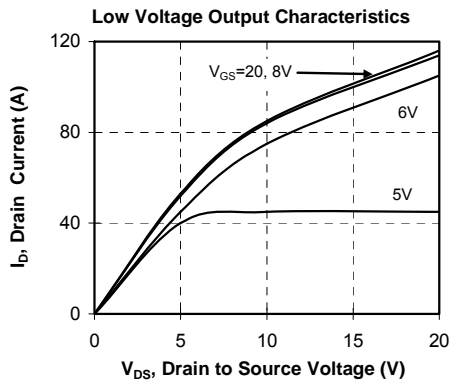
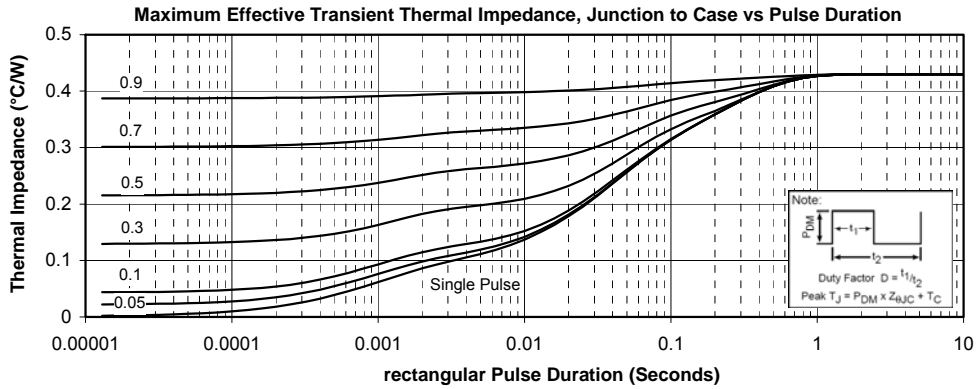
		Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance	CoolMOS		0.43	°C/W
		Diode		1.05	
$R_{thJA}$	Junction to Ambient (IGBT & Diode)			20	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-40		150	°C
$T_L$	Max Lead Temp for Soldering:0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

## SOT-227 (ISOTOP®) Package Outline

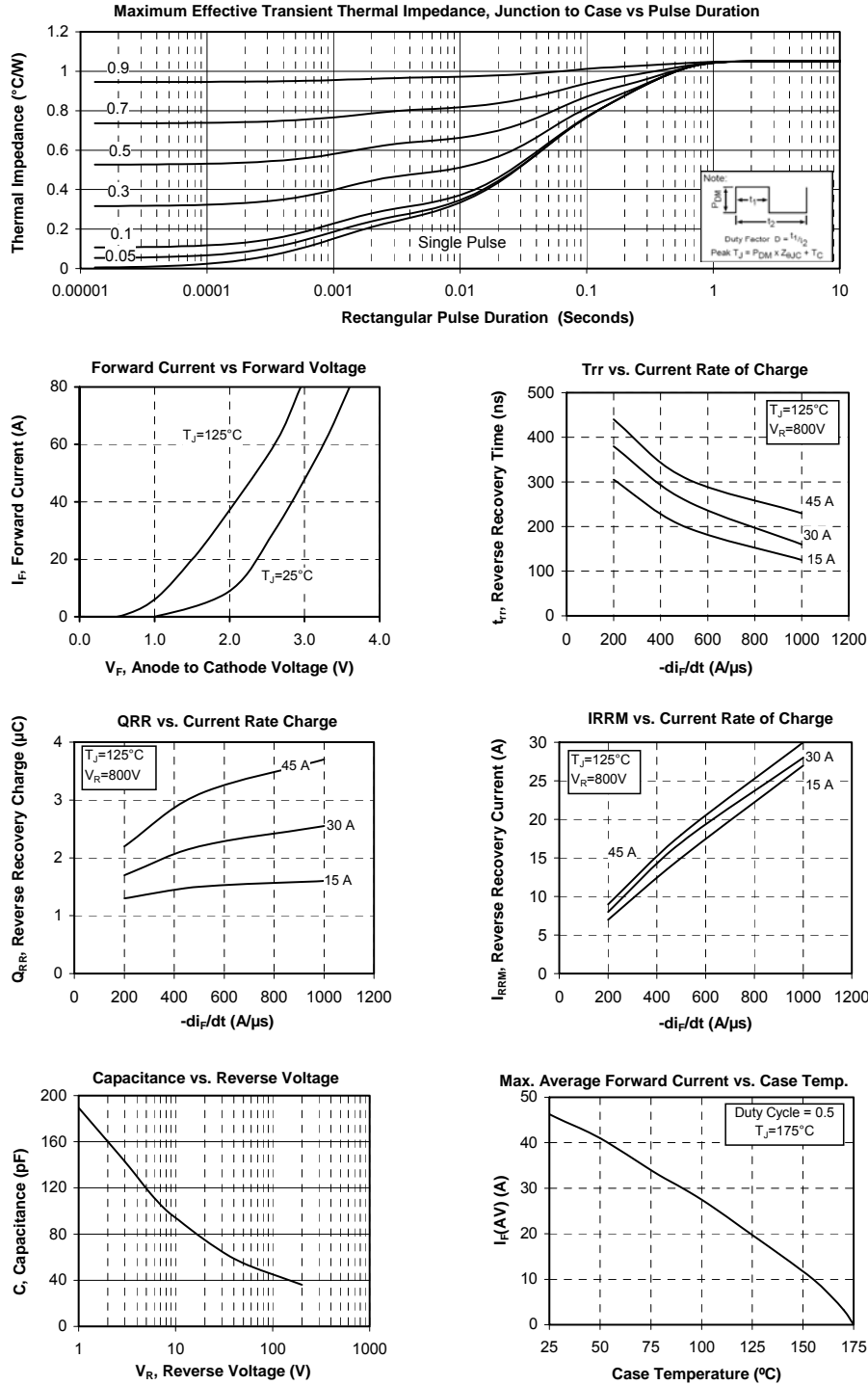


## Typical CoolMOS performance Curve





## Typical Chopper diode performance Curve



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